2021年度 提案書(Web公開用)

研究プロジェクト名: Spin transport in transition-metaldichalcogenide (TMDC)/ferromagnet bilayers

概要: <u>Current-induced spin-orbit torques</u> are promising for the efficient control of local magnetizations in spintronic devices. Recent studies suggest that <u>transition-metal-dichalcogenide</u> (<u>TMDC</u>) is not only a good candidate for generating spin-orbit torques, but also a key ingredient to promote field-free magnetization switching. <u>However, up to now, the underlying physics for the TMDC-based magnetic hetero-structures has remained elusive</u>. Specifically, the mechanism of the TMDC-based spin-orbit torques is not clear yet. Here in this proposal, we aim to <u>1</u>) prepare TMDC-based magnetic hetero-structures and 2) study the origin of current-induced spin-orbit torques.

コアメンバー:新田グループ(Tohoku Univ.)、境グループ(QST)

期待される研究成果:

- High-quality TMDC/ferromagnet bilayers will be prepared upon proper buffer layers.
- The spin Hall magneto-resistance will be studied as an initial probe of charge-spin conversion in the system.
- The current-induced spin-orbit torques will be examined in such hetero-structures to study the origin.



Figs. (a) Physical process of magnetoresistance originating from spin Hall effect. (b) Schematic demonstration of harmonic Hall technique for the spin-orbit torque study. 2020年度報告書(Web公開用)

研究プロジェクト名: Spin transport in transition-metaldichalcogenide (TMDC)/ferromagnet bilayers

概要: The spin transport properties in transition-metal-dichalcogenide (TMDC)/ferromagnet bilayers have received increasing attention in recent years because of novel physics arising from the local symmetry breaking. Particularly, the charge-spin current conversion in TMDC/ferromagnet is a promising topic because of potential applications in MRAM. However, up to now, the physical origin of the charge-spin current conversion has remained elusive. In this work, we aim to prepare TMDC-based magnetic hetero-structures and to study the spin-orbit torques of such hetero-structures.

研究成果(実施状況):

- 1. We have successfully prepared thin TMDC films on top of graphene buffer layer on a sapphire substrate. Both TMDC and graphene show good crystallinity.
- 2. We have successfully measured and analyzed the current-induced spin-orbit torques in ferromagnet (FM)/graphene bilayers by using the in-plane harmonic Hall measurements (Fig. 1). The obtained damping-like and field-like torques scale with applied current (Fig. 2).
- 3. The current-induced spin-orbit torques in graphene/TMDC/ferromagnet tri-layer samples will be studied in the future.



主要発表論文等:

研究プロジェクト名: Spin transport in transition-metaldichalcogenide (TMDC)/ferromagnet bilayers

概要: The current-induced spin-orbit torque (SOT) has been demonstrated as an efficient method to control local magnetic moments via electric means. Recently, the transition-metal-dichalcogenide (TMDC) was proposed to be a promising candidate as the SOT generator. In this proposal, we aim to prepare the TMDC materials upon proper ferromagnet (FM), and to study the related spin transport properties.

研究成果(実施状況):

主要発表論文等:

- 1. We have prepared the FM single layer and FM/graphene bilayers as an initial step, because graphene layer is found to be helpful to promote the TMDC growth.
- 2. Magneto-transport properties have been studied for FM and FM/graphene samples (Fig. 1). Relatively low resistivity below 10 $\mu\Omega$ cm and high intrinsic anomalous Hall conductivity of ~700 Ω^{-1} cm⁻¹ have been obtained as shown in Fig. 1(a) and 1(d), suggesting excellent sample quality.
- 3. We have studied the temperature dependent SOT in both FM and FM/graphene samples, the results are under discussion.
- 4. Our current study of spin transport in FM and FM/graphene samples provides a solid background for the preparation of FM/graphene/TMDC and for the study of spin transport in such tri-layers. We plan to prepare FM/graphene/TMDC tri-layers and to study the spin transport properties in the future.



Fig.1 Temperature dependence of (a) longitudinal resistivity, (b) anomalous Hall resistivity, (c) carrier density and (d) anomalous Hall scaling for FM single layer and FM/graphene bilayers (FM thickness: 10 nm).